

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Xia, et al.

Serial No.: 10/632,179

Confirmation No.: Unknown

Filed: July 31, 2003

For: Method of Decreasing the
K Value in SIOC Layer
Deposited by Chemical
Vapor Deposition

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Group Art Unit: Unknown

Examiner: Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

CERTIFICATE OF MAILING 37 CFR 1.8	
I hereby certify that this correspondence is being deposited on <u>11/18</u> , 2003 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450.	
<u>11/18/03</u> Date	<u>[Signature]</u> Signature

INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/2592.C6/KMT.

Respectfully submitted,



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U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. AMAT/2592.C6/DSM /LOW K JW	Serial No. 10/632,179
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant Xia, et al.	Confirmation No. Unknown
(Use several sheets if necessary)		Filing Date July 31, 2003	Group Unknown
Examiner Unknown			

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*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A26	5,703,404	12/30/1997	Matsuura	257	758	12/24/1996
	A27	5,700,720	12/23/1997	Hashimoto	438	622	12/20/1995
	A28	5,693,563	12/02/1997	Teong	437	190	07/15/1996
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	A30	5,679,413	10/21/1997	Petrmichle, et al.	427	534	10/11/1996
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	A34	5,616,369	04/01/1997	Williams, et al.	427	560	06/24/1994
	A35	5,598,027	01/28/1997	Matsuura	257	635	12/21/1995
	A36	5,593,741	01/14/1997	Ikeda	427	579	06/28/1995
	A37	5,578,523	11/26/1996	Fiordalice, et al.	438	633	05/18/1995
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	B15	0 469 926 A1	02/05/1992	EP	C08J	7/06	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B16	0 522 799 A2	01/13/1993	EP	H01L	21/90	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B17	0 721 019 A2	07/10/1996	EP	H01L	16/40	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B18	0 721 019 A3	07/02/1997	EP	H01L	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B19	0 711 817 A2	05/15/1996	EP	C09D	183/04	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						

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	A54	5,290,736	03/01/1994	Sato, et al.	438	761	09/24/1991
	A55	5,279,867	01/18/1994	Friedt, et al.	427	583.2	07/09/1992
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	A58	5,224,441	07/06/1993	Felts, et al.	118	718	09/27/1991
	A59	5,204,141	04/20/1993	Roberts, et al.	427	255.3	09/18/1991
	A60	5,124,014	06/23/1992	Foo, et al.	204	92.32	04/11/1991
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	A62	5,093,153	03/03/1992	Brochot, et al.	427	41	02/07/1989
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	B27	98/59089	12/30/1998	WO	C23C	16/30	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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	C3	M. Matsuura, et al. "Novel Self-Planarizing CVD Oxide for Interlayer Dielectric Applications," 1994, pages 5.7.1.-5.7.4
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.		

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	A45	5,468,520	11/21/1995	Williams, et al.	427	560	06/24/1994
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	B22	0 960 958 A2	05/27/1999	EP	C23C	16/30	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B23	0 849 789 A2	06/24/1998	EP	H01L	21/311	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B24	0 840 365 A2	05/06//1998	EP	HO1L	21/311	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B25	196 54 737 A1	07/03/1997	GERMANY	HOIL	21/31	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	B26	198 04 375 A1	01/07/1999	GERMANY	HOIL	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>

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	A65	4,981,724	01/01/1991	Hochberg, et al.	427	255.3	10/27/1988
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	A73	4,798,629	01/17/1989	Wood, et al.	106	287.16	10/22/1987
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	A75	4,557,946	12/10/1985	Sacher, et al.	427	41	06/03/1983
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	A77	4,168,330	09/18/1979	Kaganowicz	427	39	10/13/1977
	A78	2003/0032306	12/13/2003	Conti, et al.	438	778	08/10/2001
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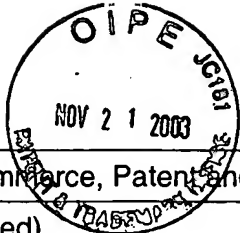
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B36						<input type="checkbox"/>	<input type="checkbox"/>

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Examiner	Date Considered
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Examiner Unknown		July 31, 2003	Unknown
OTHER ART			
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	C4	Frederic Gaillard, et al., "Silicon Dioxide Chemical Vapor Deposition Using Silane and Hydrogen Peroxide," J. Vac. Sci. Technol. Jul/Aug 1996, pages 2767-2769	
	C5	N. Inagaki et al., "Plasma Polymerization Of Organosilicon Compounds", Journal of Applied Polymer Science, Vol. 30, pp. 3385-3395 (1985)	
	C6	A. Nara, et al. "Low Dielectric Constant Insulator Formed by Downstream Plasma CVD at Room Temperature Using TMS/O ₂ ", Japanese Journal of Applied Physics, Vol. 36. No. 3B (March 1997)	
	C7	A. Grill, et al. "Low Dielectric Constant Films Prepared by Plasma-Enhanced Chemical Vapor Deposition From Tetramethylsilane", Journal of Applied Physics, Vol. 85. No. 6 (March 1999)	
	C8	Luther et al., "Planar Copper-Polyimide Back End Of The Line Interconnections For ULSI Devices", June 8-9 1993, VMIC Conference, 1993 ISMIC-102/93/0015, pp. 15-21,	
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	C14	K.H.A. Bogart, et al. "Plasma Enhanced Chemical Vapor Deposition of SiO ₂ Using Novel Alkoxysilane Precursors" Journal of Vacuum Science & Technology A 13(2) Mar/Apr 1995.	
	C15	P. Favia, "Plasma Deposition Of Thin Films From a Fluorine-Containing Cyclosiloxane", Journal Of Polymer Science: Part A: Polymer Chemistry, 1992, 10 pp.	
	C16	Y. Segui et al., "In Situ Electrical Property Measurements Of Metal (Plasma Polysiloxane)/Metal Structures", Thin Solid Films, 155 (1987) pp. 175-185, Electronics and Optics	
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>			



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Examiner Unknown			
OTHER ART			
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	C17	Y. Segui et al., "Gas Discharge In Hexamethyldisiloxane", Journal of Applied Polymer Science, Vol. 20 pp. 1611-1618 (1976)	
	C18	N. Inagaki et al., "Preparation Of Siloxane-Like Films By Glow Discharge Polymerization", Journal of Applied Polymer Science, Vol. 29, pp. 3595-3605 (1984)	
	C19	V.S. Nguyen et al., " Plasma Organosilicon Polymers", J. Electrochem. Soc. Solid-State Science and Technology, Vol. 132, No. 8, pp. 1925-1932, Aug. 1985	
	C20	K. J. Taylor et al., "Parylene Copolymers", Spring MRS, Symposium N, pp. 1-9, 1997	
	C21	S. McClatchie, et al., "Low Dielectric Constant Flowfill Technology For IMD Applications" DUMIC Conference 1997 ISMIC-222D/97/0034 (February 10-11, 1997)	
	C22	C. Rau et al, "Mechanisms Of Plasma Polymerization Of Various Silico-Organic Monomers", Thin Solid Films, pp. 28-37, 249 (1994)	
	C23	S. Sahli et al., "Properties Of Plasma-Polysiloxane Deposited By PECVD", Materials Chemistry and Physics, pp. 106-109, 33 (1993)	
	C24	A.M. Wrobel et al., "Oligomeric Products In Plasma-Polymerized Organosilicones", J. Macromol. Sci-Chem., A20 (5&6), pp. 583-618 (1983)	
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	C27	European Search Report Dated October 26, 2000	
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	C29	Laura Peters, "Pursuing the Perfect Low K Dielectrics" Semiconductor International, September 1998	
	C30	Bin Zhao, et al. "Integration of Low Dielectrics Constant Materials in Advanced Aluminum & Copper Interconnects", Materials Research Symposium Proc., Vol. 564, Materials Research Society, 1999. Pages 485-497	
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	A3	6,475,564	11/05/2002	Carter, et al.	427	249.15	07/06/2000
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	A7	6,159,871	12/12/2000	Loboda, et al.	438	786	05/29/1998
	A8	6,147,009	11/14/2000	Grill, et al.	438	780	06/29/1998
	A9	6,140,226	10/31/2000	Grill, et al.	438	637	07/30/1998
	A10	6,072,227	06/06/2000	Yau, et al.	257	642	07/13/1998
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							YES	NO
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	B2	6-163521	06/10/1994	JP (Abstract)	HOIL	21/314	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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	A17	5,858,880	01/12/1999	Dobson, et al.	438	758	01/05/1996
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	B10	01050429	02/27/1989	JP (Abstract Only)	H01L	21/318	<input checked="" type="checkbox"/>	<input type="checkbox"/>
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	B12	9-237785	09/09/1997	JP	HOIL	21/316	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B13	0 774 533 A1	05/21/1997	EP	C23C	16/40	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B14	0 519 079 A1	12/09/1991	EP	HOIL	21/312	<input type="checkbox"/>	<input checked="" type="checkbox"/>

OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	C.D. Dobson, A. Kiermasz, K. Beekman, R.J. Wilby, "Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ ," December 1994, pages 85-87

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.